

# CT430

# XtremeSense® TMR Ultra-Low Noise, <1% Total Error Current Sensor

## Features

- Integrated Contact Current Sensing for Low to Medium Current Ranges:
  - o 0 A to +20 A
  - $\circ$   $\,$  -20 A to +20 A
  - 0 A to +30 A
  - -30 A to +30 A
  - 0 A to +50 A
  - -50 A to +50 A
  - o 0 A to +65 A
  - -65 A to +65 A
- Integrated Current Carrying Conductor (CCC)
- Linear Analog Output Voltage
- Total Error Output  $\leq \pm 1.0\%$  FS, -40°C to +125°C
- 1 MHz Bandwidth
- Response Time: ~300 ns
- UL/IEC 62387 Certification
  - Rated Isolation Voltage: >5 kV<sub>RMS</sub>
  - Working Voltage for Basic Isolation: >1287 V<sub>RMS</sub>
     Working Voltage for Reinforced Isolation: >647
  - Working voltage for Reinforced Isolation: >647
     V<sub>RMS</sub>
- IEC 61000-4-5 Certification
- Low Noise: 9 mA<sub>RMS</sub> to 15 mA<sub>RMS</sub> @ f<sub>BW</sub> = 100 kHz
- Reference Voltage Output for AC/DC Current Measurements
- VOUT VREF < ±1.0% FS, -40°C to +125°C
- Immunity to Common Mode Fields: -54 dB
- Supply Voltage: 4.75 V to 5.50 V
- Over-Current Detection (OCD<sup>™</sup>)
  - Out of Range Currents
- AEC-Q100 Grade 1 (Under Qualification)
- 16-Lead SOIC-Wide Package

## Applications

- Solar/Power Inverters
- UPS, SMPS and Telecom Power Supplies
- Battery Management Systems
- Motor Control
- White Goods
- Power Utility Meters
- Over-Current Fault Protection

## **Product Description**

The CT430 is a high bandwidth and ultra-low noise integrated contact current sensor that uses Crocus Technology's patented XtremeSense® TMR technology to enable high accuracy current measurements for many consumer, enterprise, and industrial applications. It supports eight (8) current ranges where the integrated current carrying conductor (CCC) will handle up to 65 A of current and generates a current measurement as a linear analog output voltage. It achieves a total output error of less than  $\pm 1.0\%$  full-scale (FS) over voltage and the full temperature range.

It has about a 300 ns output response time while the current consumption is about 6.0 mA and is immune to common mode fields. The CT430 has an integrated over-current detection (OCD) circuitry to identify out of range <u>currents</u> (OCD) with the result outputted to the fault-bar (FLT) pin. The FLT is an open drain, active LOW digital signal that is activated by the CT430 to alert, for example a microcontroller that a fault condition has occurred.

The CT430 is offered in an industry standard 16-lead SOIC-Wide package that is "green" and RoHS compliant.

# **Part Ordering Information**

Part Number	Auto Grade	Operating Temperature Range	Current Range	Package	Packing Method			
CT430-ESWF20DR	-	-40°C to +85°C						
CT430-HSWF20DR	-	-40°C to +125°C	0 A to +20 A					
CT430-ASWF20DR	Grade 1	-40 C 10 +125 C						
CT430-ESWF20MR	-	-40°C to +85°C						
CT430-HSWF20MR	-	-40°C to +125°C	-20 A to +20 A					
CT430-ASWF20MR	Grade 1	-40 C 10 +125 C						
CT430-ESWF30DR	-	-40°C to +85°C						
CT430-HSWF30DR	-	40°C to 1425°C	0 A to +30 A					
CT430-ASWF30DR	Grade 1	-40°C to +125°C						
CT430-ESWF30MR	-	-40°C to +85°C						
CT430-HSWF30MR	-	-40°C to +125°C	-30 A to +30 A					
CT430-ASWF30MR	Grade 1	-40 C 10 +125 C		16-lead SOIC-Wide	Tana 9 Daal			
CT430-ESWF50DR	-	-40°C to +85°C		10.21 x 10.31 x 2.54 mm	Tape & Reel			
CT430-HSWF50DR	-	-40°C to +125°C	0 A to +50 A					
CT430-ASWF50DR	Grade 1	-40 C 10 +125 C						
CT430-ESWF50MR	-	-40°C to +85°C						
CT430-HSWF50MR	-	-40°C to +125°C	-50 A to +50 A					
CT430-ASWF50MR	Grade 1	-40 C 10 +125 C						
CT430-ESWF65DR	-	-40°C to +85°C						
CT430-HSWF65DR	-	40°C to 1425°C	0 A to +65 A					
CT430-ASWF65DR	Grade 1	-40°C to +125°C						
CT430-ESWF65MR	-	-40°C to +85°C						
CT430-HSWF65MR	-	-40°C to +125°C	-65 A to +65 A					
CT430-ASWF65MR	Grade 1	-40 C 10 + 125 C						

## **Evaluation Board Ordering Information**

Part Number	Current Range	Operating Temperature Range
CTD430-20DC	0 A to +20 A	
CTD430-20AC	-20 A to +20 A	
CTD430-30DC	0 A to +30 A	
CTD430-30AC	-30 A to +30 A	-40°C to +125°C
CTD430-50DC	0 A to +50 A	-40 C t0 +125 C
CTD430-50AC	-50 A to +50 A	
CTD430-65DC	0 A to +65 A	
CTD430-65AC	-65 A to +65 A	

## **Block Diagram**



Figure 1. CT430 Functional Block Diagram for 16-lead SOIC-Wide Package

# **Application Diagram**



Figure 2. CT430 Application Block Diagram

Component	Description	Vendor & Part Number	Parameter	Min.	Тур.	Max.	Unit
Свур	1.0 μF, X5R or Better	Murata GRM155C81A105KA12	C1		1.0		μF
Cfilter	Various, X5R or Better	Murata	C2		Table 2		pF
Cflt#	1.0 pF, X5R or Better	Murata GRM0335C1E102JA01	C3		1.0		nF
R <sub>FLT#</sub>	100 kΩ Pull-up Resistor	Various	R1		100		kΩ
RVREF	10 k $\Omega$ Resistor	Various	R2		10		kΩ

# **CT430** Pin Configuration



Figure 3. CT430 Pin-out Diagram for 16-lead SOIC-Wide Package (Top-Down View)

## **Pin Definition**

Pin #	Pin Name	Pin Description
1		
2	IP+	Terminal for primary conductor (positive).
3		
4		
5		
6	IP-	Terminal for primary conductor (negative).
7	16-	
8		
9	VREF	Reference voltage output. If not used, then do not connect.
10	GND	Ground.
11	FLT	<ul> <li>Active LOW output fault signal (open drain output) to indicate that the following parameters are outside of normal operational bounds:</li> <li>Over-Current Detection</li> <li>UVLO</li> <li>If not used, then a 1.0 nF capacitor must be connected from the pin to ground.</li> </ul>
12	FILTER	Filter pin to improve noise performance by connecting an external capacitor to set the cut-off frequency. If not used, then do not connect the pin (No Connect).
13	OUT	Analog output voltage that represents the measured current.
14	N/C	No connect.
15	VCC	Supply voltage.
16	N/C	No connect.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the CT430 and may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Parameter		Max.	Unit
Vcc	Supply Voltage		-0.3	6.0	V
VI/O	Analog Input/Output Pins	s Maximum Voltage	-0.3	V <sub>CC</sub> + 0.3*	V
I <sub>CCC(MAX)</sub>	Current Carrying Conduc	ctor, $T_A = +25^{\circ}C$		70	А
Vsurge	Dielectric Surge Strength Test Voltage	IEC 61000-4-5 : Tested $\pm 5$ Pulses at 2/60 seconds, 1.2 $\mu$ s (rise) and 50 $\mu$ s (width)	6.0		kV
ISURGE	Surge Strength Test Current	Tested $\pm 5$ Pulses at 3/60 seconds, 8.0 $\mu$ s (rise) and 20 $\mu$ s (width)	3.0		kA
FOD	Electrostatic Discharge	Human Body Model (HBM) per JESD22-A114	±2.0		
ESD	Protection Level	Charged Device Model (CDM) per JESD22-C101	±0.5		kV
TJ	Junction Temperature		-40	+150	°C
Tstg	Storage Temperature		-65	+155	°C
TL	Lead Soldering Tempera	Lead Soldering Temperature, 10 Seconds		+260	°C

\*The lower of  $V_{CC}$  + 0.3 V or 6.0 V.

## **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual operation of the CT430. Recommended operating conditions are specified to ensure optimal performance to the specifications. Crocus Technology does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Тур.	Max.	Unit	
Vcc	Supply Voltage Range		4.75	5.00	5.50	V
Vout	OUT Voltage Range		0		Vcc	V
Іоит	OUT Current				±1.0	mA
		Industrial	-40	+25	+85	
TA	Operating Ambient Temperature	Extended Industrial	-40	+25	+125	°C
		Automotive	-40	+25	+125	

## **Thermal Properties**

Junction-to-ambient thermal resistance is a function of application and board layout and is determined in accordance to JEDEC standard JESD51 for a four (4) layer 2s2p FR-4 printed circuit board (PCB) with 2 oz. of copper (Cu) for 20 A or 30 A and 4 oz. of copper (Cu) or more for 50 A or 65 A. Special attention must be paid not to exceed junction temperature  $T_{J(MAX)}$  at a given ambient temperature  $T_A$ .

Symbol	Parameter	Min.	Тур.	Max.	Unit
θJA_SOICW	Junction-to-Ambient Thermal Resistance, SOICW-16		119	144	°C/W
θJC_SOICW	Junction-to-Case Thermal Resistance, SOICW-16		86	112	°C/W

## **Isolation Ratings**

Symbol	Parameter	Conditions	Rating	Unit
V <sub>ISO</sub>	Rated Isolation Voltage	Agency Tested per IEC 62368* for 60 seconds. Production Tested at $V_{ISO}$ for 1 second per IEC 62368.	5.0	kV <sub>RMS</sub>
		Agency Tested per UL1577 for 60 seconds. Production Tested at $V_{\rm ISO}$ for 1 second per UL1577.	5.0	kV <sub>RMS</sub>
	Working Voltage for Basic	Tested per per IEC 62368*	1820	Vрк
Vwork_iso	Isolation		1287	VRMS
	Working Voltage for	Tootod por IEC 60260*	915	Vрк
Vwork_ri	Reinforced Isolation	Tested per IEC 62368*	647	V <sub>RMS</sub>
d <sub>CR</sub>	Creepage Distance	Minimum Distance Along Package Body from IP Pins to I/O Pins	9.21	mm
dc∟	Clearance Distance	Minimum Distance Through Air from IP Pins to I/O Pins	8.79	mm
diso	Distance Through Isolation	Minimum Internal Distance Through Isolation	110	μm
СТІ	Comparative Tracking Index	Material Group II	400 to 599	V

\*IEC 62368 is the succeeding standard to IEC 60950-1 (Edition 2) for isolation testing specifications and as such it will be compliant to the latter standard.

## **Electrical Specifications**

#### **General Parameters**

Unless otherwise specified:  $V_{CC}$  = 4.75 V to 5.50 V,  $T_A$  = -40°C to +125°C,  $C_{BYP}$  = 1.0 µF. Typical values are  $V_{CC}$  = 5.00 V and  $T_A$  = +25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit			
Power Sup	Power Supplies								
Icc	Supply Current	f <sub>BW</sub> = 1 MHz No load, I <sub>P</sub> = 0 A		6.0	9.0	mA			
Ι <sub>ουτ</sub>	OUT Maximum Drive Capability	OUT covers 10% to 90% of $V_{\rm CC}$ span.	-1.0		+1.0	mA			
CL_OUT	OUT Capacitive Load (1)				100	pF			
RL_OUT	OUT Resistive Load <sup>(1)</sup>			100		kΩ			
IVREF	VREF Maximum Drive Capability		-50		+50	μA			
CL_VREF	VREF Capacitive Load <sup>(1)</sup>				10	pF			
RL_VREF	VREF Resistive Load (1)			100		kΩ			
R <sub>FILTER</sub>	Internal Filter Resistance (1)			15		kΩ			
RIP	Primary Conductor Resistance <sup>(1)</sup>			0.5		mΩ			
PSRR	Power Supply Rejection Ratio <sup>(1)</sup>			35		dB			
SPSRR	Sensitivity Power Supply Rejection Ratio <sup>(1)</sup>			35		dB			

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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
OPSRR	Offset Power Supply Rejection Ratio <sup>(1)</sup>			40		dB
Analog Ou	tput (OUT)	·				
V <sub>OUT</sub>	OUT Voltage Linear Range	$V_{SIG_AC} = \pm 2.00 V$ $V_{SIG_DC} = \pm 4.00 V$	0.50		4.50	V
Vout_sat	Output High Saturation Voltage	V <sub>OUT</sub> , T <sub>A</sub> = +25°C,	Vcc – 0.30	Vcc – 0.25		V
CMFRR	Common Mode Field Rejection Ratio <sup>(1)</sup>			-54 0.5		dB mA/G
Reference	Voltage (VREF)		1			-
VREF	Reference Voltage	DC Current (Unipolar) AC Current (Bipolar)		0.50 2.50		- V
Fault Outp	ut (FLT)					
Vflt#_ol	FLT Voltage LOW	$I_{FLT\#\_OUT} \le 20 \ mA$	0		0.5	V
I <sub>LEAK_FLT#</sub>	High Impedance Output Leakage Current	V <sub>FLT#_OH</sub> = V <sub>CC</sub>		5		μA
RPU	FLT Pull-up Resistor			100		kΩ
Timings						
ton	Power-On Time (1)	$V_{CC} \geq 2.50 \ V$		100	200	μs
t <sub>RISE</sub>	Rise Time <sup>(1)</sup>	$I_P = I_{RANGE(MAX)},$		200		ns
tresponse	Response Time <sup>(1)</sup>	T <sub>A</sub> = +25°C,		300		ns
<b>t</b> DELAY	Propagation Delay <sup>(1)</sup>	C <sub>L</sub> = 220 pF		250		ns
t <sub>FLT#</sub>	FLT Response Time <sup>(1)</sup>			250		ns
Protection		1	T	- <u>1</u>		1
Vuvlo	Under-Voltage Lockout	Rising Vcc		2.50		V
		Falling V <sub>CC</sub>		2.45		V
Vuv_hys	UVLO Hysteresis			50		mV
locd_u	Over-Current Detection (OCD)	Rising I <sub>P</sub>		1.1 × I <sub>RANGE(MAX)</sub>		
.000_0	for DC Current (Unipolar)	Falling I <sub>P</sub>		0.9 × Irange(max)		
laas -	Over-Current Detection (OCD)	Rising I <sub>P</sub>		±1.1 × Irange(max)		_
IOCD_B	for AC Current (Bipolar)	Falling I <sub>P</sub>		±0.9 × I <sub>RANGE(MAX)</sub>		- A
IOCD_HYS	Over-Current Detection Hysteresis			0.2 × Irange(max)		Α

(1) Guaranteed by design and/or characterization; not tested in production.

## **Electrical Characteristics**



Figure 4. CT430 Supply Current vs. Temperature vs. Supply Voltage



Figure 5. CT430 Startup Waveforms for  $V_{OQ}$  = 0.50 V (DC Current)



Figure 6. CT430 Startup Waveforms for  $V_{OQ}$  = 2.50 V (AC Current)

## **Electrical Characteristics (continued)**



Figure 7. CT430 Bandwidth with C<sub>FILTER</sub> = 1.0 pF



Figure 8. CT430 Response Time;  $I_P = 50 A_{PK}$  and  $C_L = 100 pF$  (Blue =  $I_{CCC}$ , Red =  $V_{OUT}$ )



Figure 9. CT430 Rise Time;  $I_P$  = 50  $A_{PK}$  and  $C_L$  = 100 pF (Blue =  $I_{CCC}$ , Red =  $V_{OUT}$ )



Figure 10. CT430 Propagation Delay;  $I_P = 50 A_{PK}$  and  $C_L = 100 \text{ pF}$  (Blue =  $I_{CCC}$ , Red =  $V_{OUT}$ )

## **Electrical Characteristics (continued)**



Figure 11. CT430 OCD enabled at 110% of +50  $A_{\text{DC}}$  and FLT# is LOW



Figure 12. CT430 OCD disabled at 90% of +50  $A_{\text{DC}}$  and FLT# is HIGH



Figure 13. CT430 OCD enabled at +110% of +50  $A_{\text{PK}}$  and FLT# is LOW



Figure 14. CT430 OCD disabled at +90% of +50  $A_{\text{PK}}$  and FLT# is HIGH

## **Electrical Characteristics (continued)**





Figure 15. CT430 OCD enabled at -110% of -50  $A_{\text{PK}}$  and FLT# is LOW

Figure 16. CT430 OCD disabled at -90% of -50  $A_{\text{PK}}$  and FLT# is HIGH

## CT430-xSWF20DR: 0 A to +20 A

Unless otherwise specified:  $V_{CC}$  = 4.75 V to 5.50 V,  $T_A$  = -40°C to +125°C,  $C_{BYP}$  = 1.0 µF. Typical values are  $V_{CC}$  = 5.00 V and  $T_A$  = +25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
IRANGE	Current Range		0		+20	А
Voq	Voltage Output Quiescent	T <sub>A</sub> = +25°C, I <sub>P</sub> = 0 A	0.495	0.500	0.505	V
S	Sensitivity	$I_{RANGE(MIN)} \leq I_P \leq I_{RANGE(MAX)}$		200		mV/A
f <sub>BW</sub>	Bandwidth <sup>(1)</sup>	Small Signal = -3 dB		1.0		MHz
en	Noise <sup>(1)</sup>	T <sub>A</sub> = +25°C, f <sub>BW</sub> = 100 kHz		9.0		mA <sub>RMS</sub>
OUT Accu	iracy Performance					
Eout	Total Output Error	$I_P = I_{P(MAX)}$		±0.7	±1.0	% FS
ELIN	Non-Linearity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.1		% FS
Esens	Sensitivity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.7		% FS
M	Offect ) (eltere (1)	I <sub>P</sub> = 0 A,		±12.5		mV
VOFFSET	Offset Voltage (1)	T <sub>A</sub> = -40°C to +125°C		±0.3		% FS
V <sub>OUT</sub> – V <sub>RE</sub>	F Accuracy Performance					
EOUT-VREF	VOUT – VREF Error	$I_P = I_{P(MAX),} V_{CC} = 5.0 V$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			±1.0	% FS
Vout <b>-</b> Vref	OUT – VREF Offset Voltage	V <sub>CC</sub> = 5.0 V T <sub>A</sub> = -40°C to +125°C		±5.0		mV
Lifetime D	Prift	•				
ETOT_DRIFT	Total Output Error Lifetime Drift <sup>(1)</sup>	$I_{P} = I_{P(MAX)}$		±1.0		% FS

(1) Guaranteed by design and characterization; not tested in production.

## **Electrical Characteristics for CT430-xSWF20DR**



Figure 17. Total Output Error vs. Current vs. Temperature



Figure 18. VOUT – VREF Error vs. Current vs. Temperature



Figure 19. Noise Density vs. Frequency



Figure 20. CT430 Current De-rating Curve for 20 A<sub>DC</sub>

## CT430-xSWF20MR: -20 A to +20 A

Unless otherwise specified:  $V_{CC}$  = 4.75 V to 5.50 V,  $T_A$  = -40°C to +125°C,  $C_{BYP}$  = 1.0 µF. Typical values are  $V_{CC}$  = 5.00 V and  $T_A$  = +25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
RANGE	Current Range		-20		+20	А
Voq	Voltage Output Quiescent	T <sub>A</sub> = +25°C, I <sub>P</sub> = 0 A	2.495	2.500	2.505	V
S	Sensitivity	$I_{RANGE(MIN)} \leq I_P \leq I_{RANGE(MAX)}$		100		mV/A
<b>f</b> <sub>BW</sub>	Bandwidth <sup>(1)</sup>	Small Signal = -3 dB		1.0		MHz
en	Noise <sup>(1)</sup>	T <sub>A</sub> = +25°C, f <sub>BW</sub> = 100 kHz		10.0		mA <sub>RMS</sub>
OUT Accu	iracy Performance					
Eout	Total Output Error	$I_P = I_{P(MAX)}$		±0.5	±1.0	% FS
ELIN	Non-Linearity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.1		% FS
Esens	Sensitivity Error <sup>(1)</sup>	$I_P = I_{P(MAX)},$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.5		% FS
\ <i>\</i>	Off = st $(s)$ (s) (s = s = (1)	I <sub>P</sub> = 0 A,		±7.0		mV
VOFFSET	Offset Voltage <sup>(1)</sup>	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.2		% FS
V <sub>OUT</sub> – V <sub>RE</sub>	F Accuracy Performance					
EOUT-VREF	VOUT – VREF Error	$I_P = I_{P(MAX),} V_{CC} = 5.0 V$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			±1.0	% FS
Vout <b>-</b> Vref	OUT – VREF Offset Voltage	V <sub>CC</sub> = 5.0 V T <sub>A</sub> = -40°C to +125°C		±5.0		mV
Lifetime D	rift	•			•	
ETOT_DRIFT	Total Output Error Lifetime Drift <sup>(1)</sup>	$I_{P} = I_{P(MAX)}$		±1.0		% FS

(1) Guaranteed by design and characterization; not tested in production.

## **Electrical Characteristics for CT430-xSWF20MR**



Figure 21. Total Output Error vs. Current vs. Temperature



Figure 23. Noise Density vs. Frequency



Figure 22. VOUT – VREF Error vs. Current vs. Temperature



Figure 24. CT430 Current De-rating Curve for 20  $A_{\text{PK}}$  (14.1  $A_{\text{DC}})$ 

## CT430-xSWF30DR: 0 A to +30 A

Unless otherwise specified:  $V_{CC}$  = 4.75 V to 5.50 V,  $T_A$  = -40°C to +125°C,  $C_{BYP}$  = 1.0 µF. Typical values are  $V_{CC}$  = 5.00 V and  $T_A$  = +25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Irange	Current Range		0		+30	А
Voq	Voltage Output Quiescent	T <sub>A</sub> = +25°C, I <sub>P</sub> = 0 A	0.495	0.500	0.505	V
S	Sensitivity	$I_{RANGE(MIN)} \leq I_P \leq I_{RANGE(MAX)}$		133.3		mV/A
fвw	Bandwidth <sup>(1)</sup>	Small Signal = -3 dB C <sub>FILTER</sub> = 5 pF		1.0		MHz
en	Noise <sup>(1)</sup>	T <sub>A</sub> = +25°C, f <sub>BW</sub> = 100 kHz		10.0		mA <sub>RMS</sub>
OUT Accu	racy Performance	·				
Еоит	Total Output Error	$I_P = I_{P(MAX)}$		±0.7	±1.0	% FS
ELIN	Non-Linearity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.1		% FS
Esens	Sensitivity Error <sup>(1)</sup>	$I_P = I_{P(MAX)},$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.6		% FS
	$O$ ff = st $\lambda$ (site as (1)	I <sub>P</sub> = 0 A,		±13.5		mV
VOFFSET	Offset Voltage <sup>(1)</sup>	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.3		% FS
V <sub>OUT</sub> – V <sub>RE</sub>	F Accuracy Performance					
EOUT-VREF	VOUT – VREF Error	$I_P = I_{P(MAX)}, V_{CC} = 5.0 V$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			±1.0	% FS
Vout <b>-</b> Vref	OUT – VREF Offset Voltage	V <sub>CC</sub> = 5.0 V T <sub>A</sub> = -40°C to +125°C		±5.0		mV
Lifetime D	rift					
ETOT_DRIFT	Total Output Error Lifetime Drift <sup>(1)</sup>	$I_{\rm P} = I_{\rm P(MAX)}$		±1.0		% FS

(1) Guaranteed by design and characterization; not tested in production.

## **Electrical Characteristics for CT430-xSWF30DR**



Figure 25. Total Output Error vs. Current vs. Temperature







Figure 27. Noise Density vs. Frequency



Figure 28. CT430 Current De-rating Curve for 30  $A_{\text{DC}}$ 

## CT430-xSWF30MR: -30 A to +30 A

Unless otherwise specified:  $V_{CC}$  = 4.75 V to 5.50 V,  $T_A$  = -40°C to +125°C,  $C_{BYP}$  = 1.0 µF. Typical values are  $V_{CC}$  = 5.00 V and  $T_A$  = +25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
IRANGE	Current Range		-30		+30	А
Voq	Voltage Output Quiescent	T <sub>A</sub> = +25°C, I <sub>P</sub> = 0 A	2.495	2.500	2.505	V
S	Sensitivity	$I_{RANGE(MIN)} \leq I_P \leq I_{RANGE(MAX)}$		66.7		mV/A
fвw	Bandwidth <sup>(1)</sup>	Small Signal = -3 dB C <sub>FILTER</sub> = 5 pF		1.0		MHz
en	Noise <sup>(1)</sup>	T <sub>A</sub> = +25°C, f <sub>BW</sub> = 100 kHz		11.5		mA <sub>RMS</sub>
OUT Accu	racy Performance					
Еоит	Total Output Error	$I_P = I_{P(MAX)}$		±0.5	±1.0	% FS
ELIN	Non-Linearity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.1		% FS
Esens	Sensitivity Error <sup>(1)</sup>	$I_P = I_{P(MAX)},$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.4		% FS
	$O$ ff = st $\lambda$ (site set (1)	I <sub>P</sub> = 0 A,		±9.0		mV
VOFFSET	Offset Voltage (1)	T <sub>A</sub> = -40°C to +125°C		±0.2		% FS
V <sub>OUT</sub> – V <sub>RE</sub>	F Accuracy Performance					
EOUT-VREF	VOUT – VREF Error	$I_P = I_{P(MAX),} V_{CC} = 5.0 V$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			±1.0	% FS
Vout <b>-</b> Vref	OUT – VREF Offset Voltage	V <sub>CC</sub> = 5.0 V T <sub>A</sub> = -40°C to +125°C		±5.0		mV
Lifetime D	rift	•				
ETOT_DRIFT	Total Output Error Lifetime Drift <sup>(1)</sup>	$I_{P} = I_{P(MAX)}$		±1.0		% FS

(1) Guaranteed by design and characterization; not tested in production.

## **Electrical Characteristics for CT430-xSWF30MR**



Figure 29. Total Output Error vs. Current vs. Temperature







Figure 31. Noise Density vs. Frequency



Figure 32. CT430 Current De-rating Curve for 30  $A_{\text{PK}}$  (21.2  $A_{\text{DC}})$ 

## CT430-xSWF50DR: 0 A to +50 A

Unless otherwise specified:  $V_{CC}$  = 4.75 V to 5.50 V,  $T_A$  = -40°C to +125°C,  $C_{BYP}$  = 1.0 µF. Typical values are  $V_{CC}$  = 5.00 V and  $T_A$  = +25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
IRANGE	Current Range		0		+50	А
Voq	Voltage Output Quiescent	T <sub>A</sub> = +25°C, I <sub>P</sub> = 0 A	0.495	0.500	0.505	V
S	Sensitivity	$I_{RANGE(MIN)} \leq I_P \leq I_{RANGE(MAX)}$		80		mV/A
f <sub>BW</sub>	Bandwidth <sup>(1)</sup>	Small Signal = -3 dB		1.0		MHz
en	Noise <sup>(1)</sup>	T <sub>A</sub> = +25°C, f <sub>BW</sub> = 100 kHz		10.0		mA <sub>RMS</sub>
OUT Accu	iracy Performance					
Eout	Total Output Error	$I_P = I_{P(MAX)}$		±0.7	±1.5	% FS
ELIN	Non-Linearity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.2		% FS
Esens	Sensitivity Error <sup>(1)</sup>	$I_P = I_{P(MAX)},$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.6		% FS
N/	Off = st $(s)$ (s) (s = s = (1)	I <sub>P</sub> = 0 A,		±12.9		mV
VOFFSET	Offset Voltage <sup>(1)</sup>	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.3		% FS
V <sub>OUT</sub> – V <sub>RE</sub>	F Accuracy Performance					
EOUT-VREF	VOUT – VREF Error	$I_P = I_{P(MAX),} V_{CC} = 5.0 V$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			±1.0	% FS
Vout <b>-</b> Vref	OUT – VREF Offset Voltage	V <sub>CC</sub> = 5.0 V T <sub>A</sub> = -40°C to +125°C		±5.0		mV
Lifetime D	rift	•				
ETOT_DRIFT	Total Output Error Lifetime Drift <sup>(1)</sup>	$I_{P} = I_{P(MAX)}$		±1.0		% FS

(1) Guaranteed by design and characterization; not tested in production.

## **Electrical Characteristics for CT430-xSWF50DR**



Figure 33. Total Output Error vs. Current vs. Temperature







Figure 35. Noise Density vs. Frequency



Figure 36. CT430 Current De-rating Curve for 50  $A_{\text{DC}}$ 

## CT430-xSWF50MR: -50 A to +50 A

Unless otherwise specified:  $V_{CC}$  = 4.75 V to 5.50 V,  $T_A$  = -40°C to +125°C,  $C_{BYP}$  = 1.0 µF. Typical values are  $V_{CC}$  = 5.00 V and  $T_A$  = +25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
RANGE	Current Range		-50		+50	А
Voq	Voltage Output Quiescent	T <sub>A</sub> = +25°C, I <sub>P</sub> = 0 A	2.495	2.500	2.505	V
S	Sensitivity	$I_{RANGE(MIN)} \leq I_P \leq I_{RANGE(MAX)}$		40		mV/A
f <sub>BW</sub>	Bandwidth <sup>(1)</sup>	Small Signal = -3 dB		1.0		MHz
en	Noise <sup>(1)</sup>	T <sub>A</sub> = +25°C, f <sub>BW</sub> = 100 kHz		14.0		mA <sub>RMS</sub>
OUT Accu	iracy Performance					
Eout	Total Output Error	$I_P = I_{P(MAX)}$		±0.5	±1.0	% FS
ELIN	Non-Linearity Error <sup>(1)</sup>	$I_P = I_{P(MAX)},$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.1		% FS
Esens	Sensitivity Error <sup>(1)</sup>	$I_P = I_{P(MAX)},$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.5		% FS
\ <i>\</i>	$O$ ff = st $\lambda$ (site as (1)	I <sub>P</sub> = 0 A,		±10.9		mV
VOFFSET	Offset Voltage <sup>(1)</sup>	T <sub>A</sub> = -40°C to +125°C		±0.3		% FS
V <sub>OUT</sub> – V <sub>RE</sub>	F Accuracy Performance					
EOUT-VREF	VOUT – VREF Error	$I_P = I_{P(MAX),} V_{CC} = 5.0 V$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			±1.0	% FS
Vout <b>-</b> Vref	OUT – VREF Offset Voltage	V <sub>CC</sub> = 5.0 V T <sub>A</sub> = -40°C to +125°C		±5.0		mV
Lifetime D	rift	•				
ETOT_DRIFT	Total Output Error Lifetime Drift <sup>(1)</sup>	$I_{P} = I_{P(MAX)}$		±1.0		% FS

(1) Guaranteed by design and characterization; not tested in production.

## **Electrical Characteristics for CT430-xSWF50MR**



Figure 37. Total Output Error vs. Current vs. Temperature



Figure 38. VOUT – VREF Error vs. Current vs. Temperature



Figure 39. Noise Density vs. Frequency



Figure 40. CT430 Current De-rating Curve for 50  $A_{\text{PK}}$  (35.4  $A_{\text{DC}})$ 

## CT430-xSWF65DR: 0 A to +65 A

Unless otherwise specified:  $V_{CC}$  = 4.75 V to 5.50 V,  $T_A$  = -40°C to +125°C,  $C_{BYP}$  = 1.0 µF. Typical values are  $V_{CC}$  = 5.00 V and  $T_A$  = +25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
IRANGE	Current Range	0			+65	А
Voq	Voltage Output Quiescent	$T_A = +25^{\circ}C, I_P = 0 A$ 0.495		0.500	0.505	V
S	Sensitivity	$I_{RANGE(MIN)} \leq I_P \leq I_{RANGE(MAX)}$		61.5		mV/A
f <sub>BW</sub>	Bandwidth <sup>(1)</sup>	Small Signal = -3 dB		1.0		MHz
en	Noise <sup>(1)</sup>	T <sub>A</sub> = +25°C, f <sub>BW</sub> = 100 kHz		10.0		mA <sub>RMS</sub>
tip(max)	Maximum Time @ I <sub>P(MAX)</sub>					s
OUT Accu	iracy Performance					
Eout	Total Output Error	$I_{P} = I_{P(MAX)}$		±0.7	±1.5	% FS
Elin	Non-Linearity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.2		% FS
Esens	Sensitivity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.4		% FS
N/		I <sub>P</sub> = 0 A,		±3.0		mV
Voffset	Offset Voltage (1)	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.1		% FS
V <sub>OUT</sub> – V <sub>RE</sub>	F Accuracy Performance					
EOUT-VREF	VOUT – VREF Error	$I_P = I_{P(MAX),} V_{CC} = 5.0 V$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			±1.0	% FS
Vout <b>-</b> V <sub>REF</sub>	OUT – VREF Offset Voltage	V <sub>CC</sub> = 5.0 V T <sub>A</sub> = -40°C to +125°C		±5.0		mV
Lifetime D	, , , , , , , , , , , , , , , , , , ,			1	1	<u> </u>
ETOT_DRIFT	Total Output Error Lifetime Drift <sup>(1)</sup>	$I_{P} = I_{P(MAX)}$		±1.0		% FS

(2) Guaranteed by design and characterization; not tested in production.

## **Electrical Characteristics for CT430-xSWF65DR**



Figure 41. Total Output Error vs. Current vs. Temperature







Figure 43. Noise Density vs. Frequency



Figure 44. CT430 Current De-rating Curve for 65  $A_{\text{DC}}$ 

## CT430-xSWF65MR: -65 A to +65 A

Unless otherwise specified:  $V_{CC}$  = 4.75 V to 5.50 V,  $T_A$  = -40°C to +125°C,  $C_{BYP}$  = 1.0 µF. Typical values are  $V_{CC}$  = 5.00 V and  $T_A$  = +25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
IRANGE	Current Range	-65			+65	А
Voq	Voltage Output Quiescent	$T_A = +25^{\circ}C, I_P = 0 A$ 2.495		2.500	2.505	V
S	Sensitivity	$I_{RANGE(MIN)} \leq I_P \leq I_{RANGE(MAX)}$		30.8		mV/A
f <sub>BW</sub>	Bandwidth <sup>(1)</sup>	Small Signal = -3 dB		1.0		MHz
en	Noise <sup>(1)</sup>	T <sub>A</sub> = +25°C, f <sub>BW</sub> = 100 kHz		13.5		mA <sub>RMS</sub>
tip(max)	Maximum Time @ I <sub>P(MAX)</sub>					s
OUT Accu	racy Performance					
Eout	Total Output Error	$I_{P} = I_{P(MAX)}$		±0.5	±1.0	% FS
Elin	Non-Linearity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.2		% FS
Esens	Sensitivity Error <sup>(1)</sup>	$I_{P} = I_{P(MAX)},$ $T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		±0.3		% FS
	Off	I <sub>P</sub> = 0 A,		±3.0		mV
Voffset	Offset Voltage <sup>(1)</sup>	T <sub>A</sub> = -40°C to +125°C		±0.1		% FS
V <sub>OUT</sub> – V <sub>RE</sub>	F Accuracy Performance			•		
EOUT-VREF	VOUT – VREF Error	$I_P = I_{P(MAX),} V_{CC} = 5.0 V$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			±1.0	% FS
Vout -	OUT – VREF Offset	V <sub>CC</sub> = 5.0 V		15.0		
$V_{REF}$	Voltage	T <sub>A</sub> = -40°C to +125°C		±5.0		mV
Lifetime D	rift					
ETOT_DRIFT	Total Output Error Lifetime Drift <sup>(1)</sup>	$I_P = I_{P(MAX)}$		±1.0		% FS

(2) Guaranteed by design and characterization; not tested in production.

## **Electrical Characteristics for CT430-xSWF65MR**







Figure 46. VOUT – VREF Error vs. Current vs. Temperature



Figure 47. Noise Density vs. Frequency



Figure 48. CT430 Current De-rating Curve for 65  $A_{\text{PK}}$  (46.0  $A_{\text{DC}})$ 

#### Overview

The CT430 is a very high accuracy contact current sensor with an integrated current carrying conductor (CCC) that handles up to 65 A. It has very high sensitivity and a wide dynamic range with excellent accuracy (very low total output error) across temperature. This current sensor supports eight (8) current ranges:

- 0 A to +20A
- -20 A to +20 A
- 0 A to +30 A
- -30 A to +30 A
- 0 A to +50 A
- -50 A to +50 A
- 0 A to +65 A
- -65 A to +65 A

When current is flowing through the CCC, the XtemeSense TMR sensors inside the chip senses the field which in turn generates differential voltage signals that then goes through the Analog Front-End (AFE) to output a current measurement with less than  $\pm 1.0\%$  Full-Scale (FS) total output error (E<sub>OUT</sub>).

The chip is designed to enable a very fast response time of 300 ns for the current measurement from the OUT pin as the bandwidth for the CT430 is 1.0 MHz. Even with a high bandwidth, the chip consumes a minimal amount of power.

## Linear Output Current Measurement

The CT430 provides a continuous linear analog output voltage which represents the current measurement. The output voltage range of OUT is from 0.50 V to 4.50 V with a  $V_{OQ}$  of 0.50 V and 2.50 V for unidirectional and bidirectional currents, respectively. Figure 49 illustrates the output voltage range of the OUT pin as a function of the measured current.





## Filter Function (FILTER)

The CT430 has a pin for the FILTER function which will enable it to improve the noise performance by changing the cut-off frequency. The bandwidth of the CT430 is 1.0 MHz however by adding a capacitor to the FILTER pin which will be in series with an internal resistance of approximately 15 k $\Omega$  will set the cut-off frequency to reduce the noise.

Table 2 shows the capacitor values required to achieve four (4) cut-off frequencies.

Cut-off Frequency	C <sub>FILTER</sub> (pF)	Capacitor Part Number
100 kHz	91	GRM0225C1C910JA02
250 kHz	33	GRM0225C1C330JA02
500 kHz	16	GRM0225C1C160JA03
1.0 MHz	5	GRM0225C1C5R0CA03

#### Table 2. R-C Filter Options for FILTER Pin

If the FILTER pin is not used, then it should be left unconnected (No Connect).

## Voltage Reference Function (VREF)

The CT430 has a reference voltage (VREF) pin that may be used as an output voltage reference for AC or DC current measurements. The VREF pin should be connected to a buffer circuit.

If the VREF is not used, then it should be left unconnected.

#### Sensitivity

The Sensitivity (S) is a change in CT430's output in response to a change in 1 A of current flowing through the CCC. It is defined by the product of the magnetic circuit sensitivity (G/A, where 1.0 G = 0.1 mT) and the chip's linear amplifier gain (mV/G). Therefore, the result of this gives a sensitivity unit of mV/A. The CT430 is factory calibrated to optimize the sensitivity for the full scale of the device's dynamic range.

#### **Total Output Error**

The Total Output Error is the difference between the current measured by CT430 and the actual current, relative to the actual current. It is equivalent to the ratio between the difference of the ideal and actual voltage to the ideal sensitivity multiplied by the current flowing through the primary conductor (CCC). The following

equation defines the Total Output Error ( $E_{OUT}$ ) for the CT430:

$$E_{OUT} = \frac{V_{IOUT\_IDEAL}(I_P) - V_{IOUT}(I_P)}{S_{IDEAL}(I_P) \times I_P}$$

The  $E_{OUT}$  incorporates all sources of error and is a function of the sensed current (I<sub>P</sub>) from CT430. At high current levels, the  $E_{OUT}$  will be dominated by the sensitivity error whereas at low current, the dominant characteristic is the offset voltage. Figure 50 shows the behavior of  $E_{OUT}$  versus I<sub>P</sub>. When I<sub>P</sub> goes to 0 from both directions, the curves exhibit asymptotic behavior i.e.,  $E_{OUT}$  approaches infinity.



# Figure 50. Total Output Error $(E_{OUT})$ vs. Sensed Current (IP)

The CT430 achieves a total output error ( $E_{OUT}$ ) that is less than ±1.0% of Full-Scale (FS) over supply voltage and temperature. It is designed with innovative and proprietary TMR sensors and circuit blocks to provide very accurate current measurements regardless of the operating conditions.

#### **Sensitivity Error**

The sensitivity error ( $E_{\text{SENS}}$ ) is the sensitivity temperature drift error for unipolar or DC current. It is calculated using the equation below:

$$E_{SENS} = \left(\frac{S_{MEASURED}}{S} - 1\right) \times 100\%$$

For bipolar or AC current, the E<sub>SENS</sub> is calculated by dividing the equation by 2.

#### Power-On Time (ton)

The Power-On Time ( $t_{ON}$ ) of 100 µs is the amount of time required by CT430 to start up, fully power the chip and becoming fully operational from the moment the supply voltage is greater than the UVLO voltage. This time includes the ramp up time and the settling time (within 10% of steady-state voltage) after the power supply has reached the minimum V<sub>CC</sub>.

#### **Response Time (tresponse)**

The Response Time ( $t_{RESPONSE}$ ) of 300 ns for the CT430 is the time interval between the following terms:

- 1. When the primary current signal reaches 90% of its final value,
- 2. When the chip reaches 90% of its output corresponding to the applied current.



Figure 51. CT430 Response Time Curve

#### Rise Time (trise)

The CT430's rise time,  $t_{\text{RISE}}$ , is the time interval of when it reaches 10% and 90% of the full-scale output voltage. The  $t_{\text{RISE}}$  of the CT430 is 200 ns.

## Propagation Delay (tDELAY)

The Propagation Delay  $(t_{\text{DELAY}})$  is the time difference between these two events:

- 1. When the primary current reaches 20% of its final value
- 2. When the chip reaches 20% of its output corresponding to the applied current.

The CT430 has a propagation delay of 250 ns.



Figure 52. CT430 Propagation Delay and Rise Time Curve

## **Over-Current Detection (OCD)**

The Over-Current Detection (OCD) circuitry detects measured current values that are 110% above the maximum current range value of the CT430 for the unipolar (DC current) variant. For the bipolar (AC current) variant of the CT430 it is greater than  $\pm$ 110% of the maximum current range. This will generate a fault signal via the Fault# Interrupt (FLT) pin (LOW) to the host system's microcontroller. Once the measured current falls to 90% of the maximum current range for the DC current variant or  $\pm$ 90% for the AC current version then the fault will be cleared, and the FLT pin will go HIGH.

## Under-Voltage Lockout (UVLO)

The Under-Voltage Lock-out protection circuitry of the CT430 is activated when the supply voltage (V<sub>CC</sub>) falls below 2.45 V. The CT430 remains in a low quiescent state until V<sub>CC</sub> rises above the UVLO threshold (2.50 V). In this condition where the V<sub>CC</sub> is less than 2.45 V and UVLO is triggered, the output from the CT430 is not valid and the FLT pin will go LOW. Once the V<sub>CC</sub> rises above 2.50 V then the UVLO is cleared, and the FLT pin will be HIGH.

## Fault# Interrupt (FLT)

The CT430 generates an active LOW digital fault signal via the FLT pin to interrupt the microcontroller to indicate a fault event has been triggered. It is an open drain output and requires a pull-up resistor with a value of 100 k $\Omega$  tied

to  $V_{CC}$  and a 1.0 nF capacitor is connected to ground. A fault signal will interrupt the host system for these events:

- OCD
- UVLO

The FLT signal will be asserted LOW whenever one of the above fault events occur. In the case of an UVLO event, the FLT pin will stay LOW until the fault is cleared and then go HIGH.

If the FLT is not used, then a 1.0 nF capacitor must be connected from the pin to ground.

#### Immunity to Common Mode Fields

The CT430 is housed in custom plastic package that utilizes a "U-shaped" lead-frame to reduce the common mode fields generated by external stray magnetic fields. With the "U-shaped" lead-frame, the stray fields cancel one another thus reducing electro-magnetic interference (EMI). The CT430 is able to achieve -54 dB of Common Mode Rejection Ratio (CMFRR).

Also, good PCB layout of the CT430 will optimize performance and reduce EMI. Please see the Applications Information section in this data sheet for recommendations on PCB layout.

#### Creepage and Clearance

Two important terms as it relates to isolation provided by the package are: creepage and clearance. Creepage is defined as the shortest distance across the surface of the package from one side the leads to the other side of the leads. The definition for clearance is the shortest distance between the leads of opposite side through the air. Figure 53 illustrates the creepage and clearance for the SOICW-16 package of the CT430.



Figure 53. The Creepage and Clearance for the CT430's SOICW-16 package





#### Figure 54. CT430 Application Block Diagram

#### Application

The CT430 is an integrated contact current sensor that can be used in many applications from measuring current in power supplies to motor control to over-current fault protection. It is a plug-and-play solution in that no calibration is required and it outputs to a microcontroller a simple linear analog output voltage which corresponds to a current measurement value. A second output called FLT# alerts the host system to any fault event that may occur in the CT430. Figure 54 is an application diagram of how CT430 would be implemented in a system. The third output is the VREF which provides the output reference voltage of the CT430.

It is designed to support an operating voltage range of 4.75 V to 5.50 V, but it is ideal to use a 5.0 V power supply where the output tolerance is less than  $\pm 5\%$ .

#### **Bypass Capacitor**

A single 1.0  $\mu$ F capacitor is needed for the VCC pin to reduce the noise from the power supply and other circuits. This capacitor should be placed as close as possible to the CT430 to minimize inductance and resistance between the two devices.

#### **Filter Capacitor**

A capacitor may be added to the FILTER pin of the CT430 if there is a requirement to improve the noise

performance. The capacitor will be connected to an internal resistor of 15 k $\Omega$  inside the chip to form a R-C filter. This R-C filter produces a cut-off frequency that will reduce the noise over this lower bandwidth.

If the FILTER pin is not used, then it should not be connected (No Connect).

#### **FLT** and VREF Resistors and Capacitors

For the CT430, the FLT# pin is an open drain output. It requires a pull-up resistor value of 100 k $\Omega$  to be connected from the pin to V<sub>CC</sub> and also a 1.0 nF capacitor to be connected from the pin to ground.

In designs where the VREF pin is used, a 10 k $\Omega$  resistor must be connected as close to the pin as possible in series with a load.

If the VREF pin is not needed in the application, then this pin should not be connected and be left floating.

Also, if the FLT# pin function is not required in the application, then a 1.0 nF capacitor must be connected from this pin to ground.

#### **Recommended PCB Layout**

Since the CT430 can measure up to 65 A of current, special care must be taken in the printed circuit board (PCB) layout of the CT430 and the surrounding circuitry. It is recommended that the CCC pins be connected to as

# CT430

much copper area as possible. For up to 30 A of current, 2 oz (or heavier) of copper can be used for the PCB traces. It is also recommended that 4 oz. or heavier copper be used for PCB traces when the CT430 is used to measure 50 A and 65 A of current. Additional layers of the PCB should also be used to carry current and be connected using the arrangement of vias.

Figure 55 and Figure 56 show the recommended the PCB layout for the 20 A, 30 A, 50 A and 65 A variants of the CT430. Please note that the traces connected to the IP+ and IP- pins of the CT430 are very wide with multiple vias such that it can handle the high current.



Figure 55. Recommended PCB Layout (Top Layer) for the 20 A to 65 A variants of the CT430.



Figure 56. Recommended PCB Layout (Bottom Layer) for the 20 A to 65 A variants of the CT430.

## **SOICW-16 Package Drawing and Dimensions**



#### NOTES

#### 1. ALL DIMENSIONS IN MM.

- 2. PACKAGE SURFACE FINISHING: 2.1. TOP : MATTE (CHARMILLES #18~30) 2.2. BOTTOM : MATTE (CHARMILLES #12~27)
- 3. LEAD COPLANARITY SHOULD BE OT 0.10M MAX. 4. ALL DIMENSIONS EXCLUDING MOLD FLASHES AND END FLASH FROM THE PACKAGE BODY SHALL NOT EXCEED 0.25MM PER SIDE (D)

#### Figure 57. SOICW-16 Package Drawing

Symbol	Dimensions in Millimeters (mm)								
Symbol	Min.	Тур.	Max.						
А	2.44	2.54	2.64						
A1	0.10	0.20	0.30						
A2	2.24	2.34	2.44						
b	0.36	0.41	0.46						
С	0.24	0.25	0.26						
D	10.11 10.21		10.31						
E	7.40	7.50 7.60							
е		1.27 BSC							
Н	10.11	10.31	10.51						
h	0.31	0.51	0.71						
J	0.53	0.63	0.73						
K		7° BSC							
L	0.51	0.76	1.01						
R	0.63	0.76	0.89						
ZD		0.66 REF							
α	0°	-	8°						

#### Table 3. CT430 SOICW-16 Package Dimensions

Crocus Technology provides package drawings as a service to customers considering or planning to use Crocus products in their designs. Drawings may change without notice. Please note the revision and date of the data sheet and contact a Crocus Technology representative to verify or obtain the most recent version. The package specifications do not expand the terms of Crocus Technology's worldwide terms and conditions, specifically the warranty therein, which covers Crocus Technology's products.

## SOICW-16 Tape & Pocket Drawing and Dimensions



Ao	10.90 +/- 0.1
Bo	10.70 +/- 0.1
Ko	3.00 +/- 0.1
F	7.50 +/- 0.1
P 1	12.00 +/- 0.1
W	16.00 +/- 0.3

Figure 58. SOICW-16 Package Drawing

**CT430 Tape Pocket Orientation** 



Figure 59. SOICW-16 Orientation in Tape Pocket

- Measured from centreline of sprocket hole (I)
- to centreline of pocket. (II)
- Cumulative tolerance of 10 sprocket holes is  $\pm$  0.20 . (III) Measured from centreline of sprocket
- hole to centreline of pocket. Other material available.
- (IV)
- Typical SR of form tape Max 10<sup>9</sup> OHM/SQ (V)
- ALL DIMENSIONS IN MILLIMETRES UNLESS OTHERWISE STATED.

# **Package Information**

## Table 4. CT430 Package Information

Part Number	Package Type	# of Leads	Quantity per Reel	Lead Finish	MSL Rating <sup>(2)</sup>	Operating Temperature <sup>(3)</sup>	Device Marking <sup>(4)</sup>
CT430-ESWF20DR	SOIC-W	16	1,000	Sn	3	-40°C to +85°C	CT430 SWF20DR YYWWLL
CT430-HSWF20DR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430 SWF20DR YYWWLL
CT430-ASWF20DR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430A SWF20DR YYWWLL
CT430-ESWF20MR	SOIC-W	16	1,000	Sn	3	-40°C to +85°C	CT430 SWF20MR YYWWLL
CT430-HSWF20MR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430 SWF20MR YYWWLL
CT430-ASWF20MR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430A SWF20MR YYWWLL
CT430-ESWF30DR	SOIC-W	16	1,000	Sn	3	-40°C to +85°C	CT430 SWF30DR YYWWLL
CT430-HSWF30DR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430 SWF30DR YYWWLL
CT430-ASWF30DR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430A SWF30DR YYWWLL
CT430-ESWF30MR	SOIC-W	16	1,000	Sn	3	-40°C to +85°C	CT430 SWF30MR YYWWLL
CT430-HSWF30MR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430 SWF30MR YYWWLL
CT430-ASWF30MR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430A SWF30MR YYWWLL
CT430-ESWF50DR	SOIC-W	16	1,000	Sn	3	-40°C to +85°C	CT430 SWF50DR YYWWLL

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Part Number	Package Type	# of Leads	Quantity per Reel	Lead Finish	MSL Rating <sup>(2)</sup>	Operating Temperature <sup>(3)</sup>	Device Marking <sup>(4)</sup>
CT430-HSWF50DR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430 SWF50DR YYWWLL
CT430-ASWF50DR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430A SWF50DR YYWWLL
CT430-ESWF50MR	SOIC-W	16	1,000	Sn	3	-40°C to +85°C	CT430 SWF50MR YYWWLL
CT430-HSWF50MR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430 SWF50MR YYWWLL
CT430-ASWF50MR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430A SWF50MR YYWWLL
CT430-ESWF65DR	SOIC-W	16	1,000	Sn	3	-40°C to +85°C	CT430 SWF65DR YYWWLL
CT430-HSWF65DR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430 SWF65DR YYWWLL
CT430-ASWF65DR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430A SWF65DR YYWWLL
CT430-ESWF65MR	SOIC-W	16	1,000	Sn	3	-40°C to +85°C	CT430 SWF65MR YYWWLL
CT430-HSWF65MR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430 SWF65MR YYWWLL
CT430-ASWF65MR	SOIC-W	16	1,000	Sn	3	-40°C to +125°C	CT430A SWF65MR YYWWLL

(1) RoHS is defined as semiconductor products that are compliant to the current EU RoHS requirements. It also will meet the requirement that RoHS substances do not exceed 0.1% by weight in homogeneous materials. Green is defined as the content of Chlorine (CI), Bromine (Br) and Antimony Trioxide based flame retardants satisfy JS709B low halogen requirements of ≤ 1,000 ppm.

(2) MSL Rating = Moisture Sensitivity Level Rating as defined by JEDEC standard classifications.

(3) Package will withstand ambient temperature range of -40°C to +125°C and storage temperature range of -65°C to +150°C.

(4) Device Marking for CT430 is defined as CT430 SWFxxZR YYWWLL where the first 2 lines = part number, YY = year, WW = work week and LL = lot code.

# CT430

## **Device Marking**



Row No.	Code	Definition
3	•	Pin 1 Indicator
1	CT430	Crocus Part Number
2	PKG	Package Type
2	XX	Maximum Current Rating
2	ZR	Current Range
3	YY	Calendar Year
3	WW	Work Week
3	LL	Lot Code

Table 5. CT430 Device Marking Definition for 16-leadSOIC-W Package

Figure 60. CT430 Device Marking for 16-lead Package

## Part Number Ordering Legend



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